TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

2SC3419

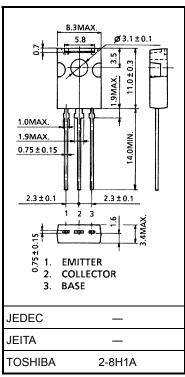
Medium-Power Amplifier Applications.

Unit: mm

- Low saturation voltage: VCE (sat) = 0.25 V (typ.) (IC = 500 mA, IB = 50 mA)
- High collector power dissipation: PC = 1.2 W (Ta = 25°C)
- Complementary to 2SA1356

Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	40	V	
Collector-emitter voltage		V _{CEO}	40	V	
Emitter-base voltage		V _{EBO}	5	V	
Collector current		I _C	800	mA	
Base current		Ι _Β	80	mA	
Collector power dissipation	Ta = 25°C	Pc	1.2	W	
	Tc = 25°C	FC	5		
Junction temperature		Тј	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



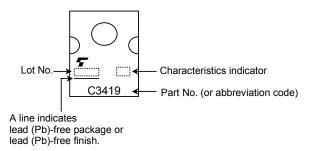
Weight: 0.82 g (typ.)

Electrical Characteristics (Tc = 25°C)

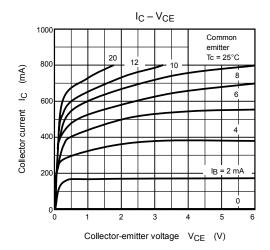
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 40 V, I _E = 0	_	_	1.0	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	1.0	μA
Collector-emitter breakdown voltage	V _{CEO}	I _C = 10 mA, I _B = 0	40	_	_	V
DC current gain	h _{FE (1)} (Note)	V _{CE} = 2 V, I _C = 50 mA	70	_	240	
	h _{FE (2)}	V _{CE} = 2 V, I _C = 0.8 A	13	60	_	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 500 mA, I _B = 50 mA	_	0.25	0.8	V
Base-emitter voltage	V _{BE}	V _{CE} = 2 V, I _C = 500 mA	_	0.90	1.1	V
Transition frequency	f _T	V _{CE} = 2 V, I _C = 0.5 A	50	100	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	10	_	pF

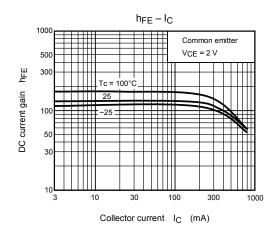
Note: h_{FE} (1) classification O: 70 to 140, Y: 120 to 240

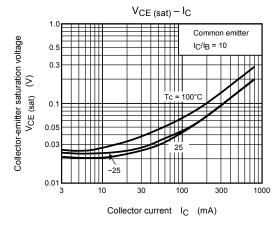
Marking

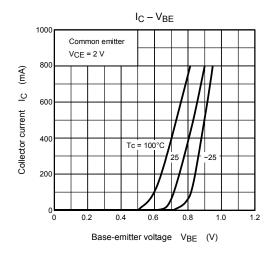


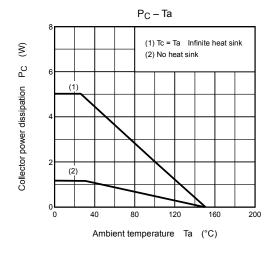
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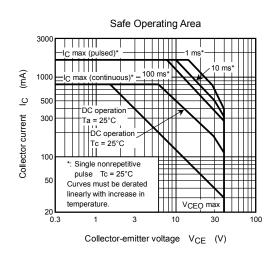












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